



JUNCTION FIELD EFFECT TRANSISTOR **2SK3230**

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK3230 is suitable for converter of ECM.

FEATURES

- Compact package
- High forward transfer admittance 1000 μS TYP. (IDSS = 100 μA) 1600 μS TYP. (IDSS = 200 μA)
- Includes diode and high resistance at G S

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3230	SC-89 (TUSM)		

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage Note1	VDSX	20	V
Gate to Drain Voltage	Vgdo	-20	V
Drain Current	lo	10	mA
Gate Current	lg	10	mA
Total Power Dissipation Note2	Рт	200	mW
Junction Temperature	Tj	125	°C
Storage Temperature	Tstg	-55 to +125	°C

PACKAGE DRAWING (Unit: mm)





EQUIVALENT CIRCUIT



Notes 1. Vgs = -1.0 V

2. Mounted on ceramic substrate of 3.0 cm² x 0.64 mm

Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

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ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	IDSS	$V_{DS} = 5.0 V, V_{GS} = 0 V$	40		600	μA
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 1.0 \ \mu\text{A}$	-0.1		-1.0	V
Forward Transfer Admittance	y _{fs1}	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 30 \ \mu\text{A}, \text{ f} = 1.0 \text{ kHz}$	350			μS
Forward Transfer Admittance	yfs2	$V_{DS} = 5.0 V, V_{GS} = 0 V, f = 1.0 \text{ kHz}$	350			μS
Input Capacitance	Ciss	$V_{DS} = 5.0 V, V_{GS} = 0 V, f = 1.0 MHz$		7.0	8.0	pF
Noise Voltage	NV	See Test Circuit		1.8	3.0	μV

IDSS RANK

MARKING	J2	J3	J4	J5	J6	J7
loss (μA)	40 to 70	60 to 110	90 to 180	150 to 300	200 to 450	300 to 600

NOISE VOLTAGE TEST CIRCUIT



TYPICAL CHARACTERISTICS (TA = 25°C)













VGS - Gate to Source Voltage - V

INPUT CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE





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